

Abstract of the Disclosure

Method for selectively removing material from the surface of a substrate, masking material for a wafer, and wafer with masking material

A method for the selective removal of material from a substrate surface for forming a deepening comprises the steps of applying a mask onto the substrate surface in accordance with the desired selective removal and dry-etching the substrate, a metal, preferably aluminum, being used as the masking material. Power may be coupled inductively to a plasma.